

**SPECIFICATION AMENDMENTS:**

Please amend the specification as follows:

Page 10, line 18, through line 28, please amend the current paragraph as follows:

The n-type GaAs layer 111 has a thickness of about 10nm (= 0.01  $\mu\text{m}$ ), the n-type  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  layer 112 has a thickness of about 0.5  $\mu\text{m}$ , the n-type  $\text{Al}_y\text{Ga}_{1-y}\text{As}$  layer 113 has a thickness of about 1  $\mu\text{m}$ , and the n-type  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  layer 114 has a thickness of about 0.5  $\mu\text{m}$ . In this case, the thickness of the LED epitaxial film 110 becomes about 2  $\mu\text{m}$ . However, the thicknesses of the above layers are not limited to the above values. Further, the material of the LED epitaxial film 110 may be replaced by other material, e.g., a compound semiconductor, such as  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ , where  $0 \leq x \leq 1$  and  $0 \leq z \leq 1$ , in this case, GaN, AlGaIn, or InGaIn.